

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of:

Docket No. P27154

Michael P. Belyansky, *et al.*

Confirmation No. 2429

Group Art Unit: 2818

Appln. No. : 10/708,430

Examiner: A. Huynh

Filed : March 3, 2004

For : **MOBILITY ENHANCED CMOS DEVICES**

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
U.S. Patent and Trademark Office  
Customer Service Window, Mail Stop \_\_\_\_\_  
Randolph Building  
401 Dulany Street  
Alexandria VA 22314

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, and supplemental to the Information Disclosure Statement filed on December 13, 2005, applicant respectfully brings the following documents, listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application.

Further to the U.S. Patent and Trademark Office's decision to waive the requirement under 37 C.F.R. § 1.98 (a)(2)(i), copies of the U.S. patents and U.S. published patent applications are not enclosed herewith. However, if any copies are needed, the Examiner is respectfully requested to contact the undersigned.

Applicants respectfully request that the Examiner consider the materials cited and indicate such consideration by appropriately initialing the enclosed PTO-1449 Form and including a copy of the initialed form in the next official communication.

Applicants note that a Petition to Withdraw the Application from issue and a Request for Continued Examination (RCE) have been filed with the Office of Petitions on even date. Therefore, copies these documents are enclosed.

Applicants acknowledge that this Supplemental Information Disclosure Statement (SIDS) is being filed after payment of the issue fee. However, Applicants are concurrently filing this SIDS as a submission to the filing of a Request for Continued Examination (RCE) along with the fee for filing an RCE, and a petition to request withdrawal of the application from issue. Accordingly, Applicant respectfully requests consideration of the above-noted documents.

Should there be any questions concerning this application, the Examiner is invited to contact the undersigned at the below listed telephone number.

Respectfully submitted,  
Michael P. Belyansky, *et al*

A handwritten signature in black ink, appearing to read 'Andrew M. Calderon', is written over a horizontal line.

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FORM PTO-1449  U.S. Department of Commerce Patent and Trademark Office  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Atty. Docket No. P27154	Application No.
	Applicant Michael P. Belyansky et al.	
	Filing Date March 3, 2004	Group 2818

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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## FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
JP 64-76755	3-22-1989	Japan			X

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant			
				Filing Date		Group	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." 1989 IEEE, Paper 6.2, pp. 140-143.					
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EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							